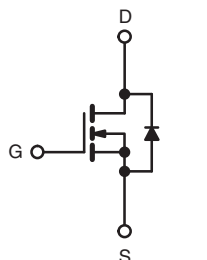
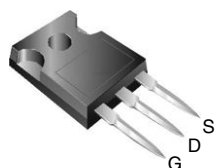


D Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	450	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.17
Q_g max. (nC)	88	
Q_{gs} (nC)	12	
Q_{gd} (nC)	23	
Configuration	Single	

TO-247AC


N-Channel MOSFET

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Optimal Design
 - Low Area Specific On-Resistance
 - Low Input Capacitance (C_{iss})
 - Reduced Capacitive Switching Losses
 - High Body Diode Ruggedness
 - Avalanche Energy Rated (UIS)
- Optimal Efficiency and Operation
 - Low Cost
 - Simple Gate Drive Circuitry
 - Low Figure-of-Merit (FOM): $R_{on} \times Q_g$
 - Fast Switching
- Compliant to RoHS Directive 2011/65/EU



RoHS*
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Consumer Electronics
 - Displays (LCD or Plasma TV)
- Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
- SMPS

ORDERING INFORMATION

Package	TO-247AC
Lead (Pb)-free	SiHG25N40D-E3
Lead (Pb)-free and Halogen-free	SiHG25N40D-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	400	V
Gate-Source Voltage	V_{GS}	± 30	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	78	
Linear Derating Factor		2.2	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	556	mJ
Maximum Power Dissipation	P_D	278	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	dV/dt	24	V/ns
Reverse Diode dV/dt		0.6	
Soldering Recommendations (Peak Temperature)		300°	°C

Notes

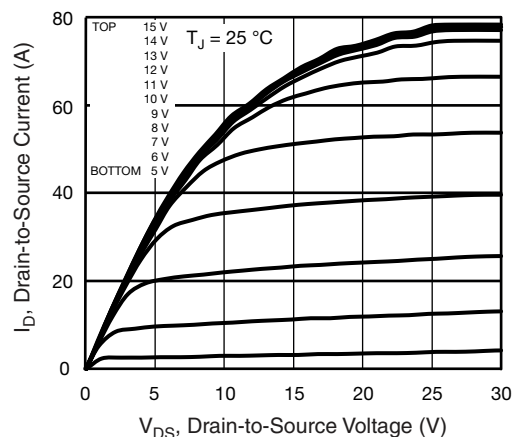
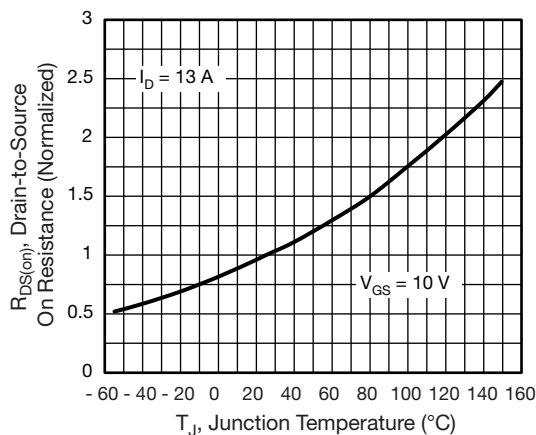
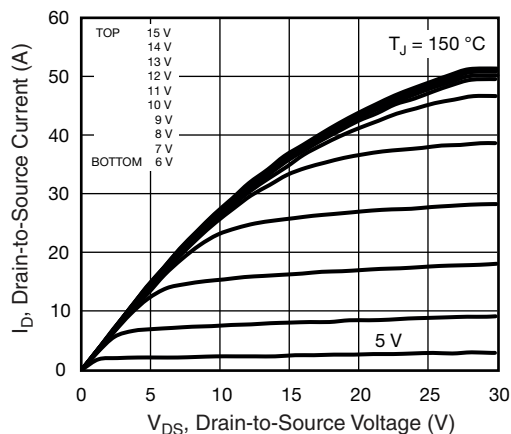
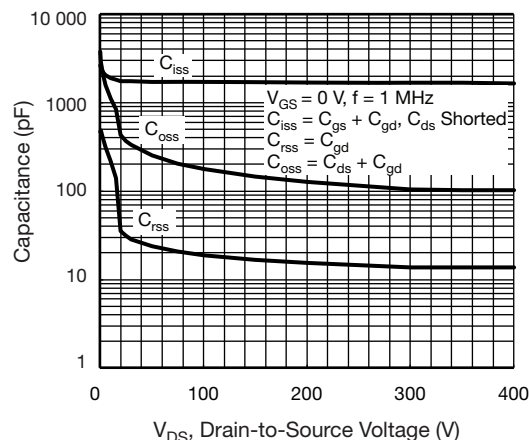
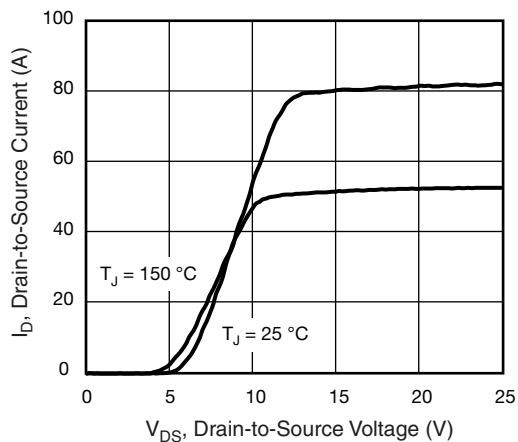
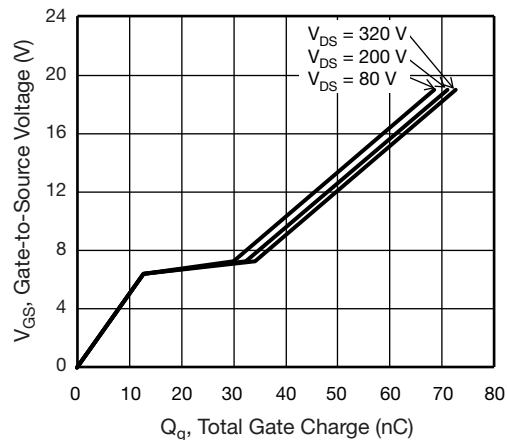
- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 2.3$ mH, $R_g = 25$ Ω , $I_{AS} = 17$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, starting $T_J = 25$ °C.

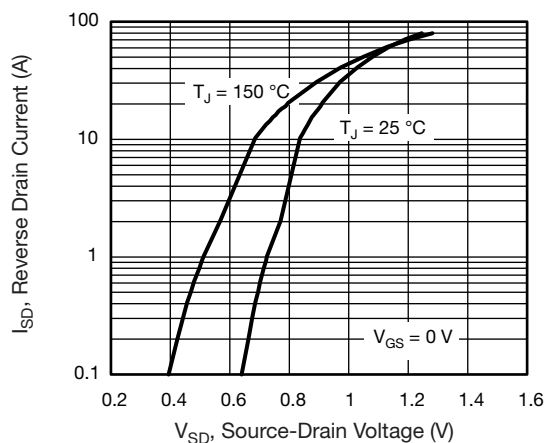
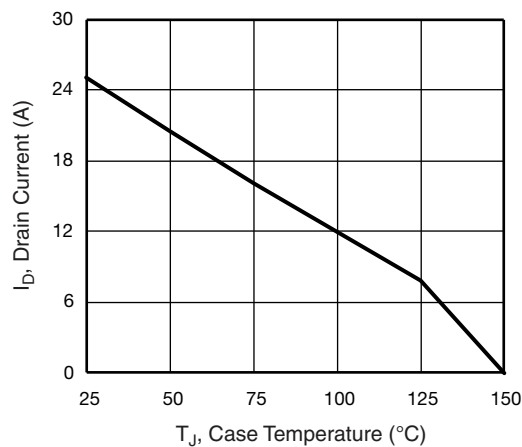
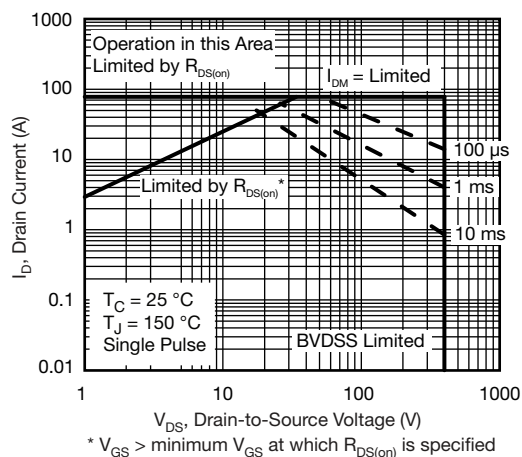
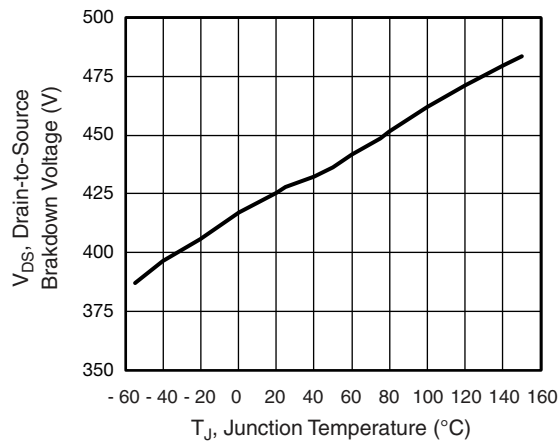
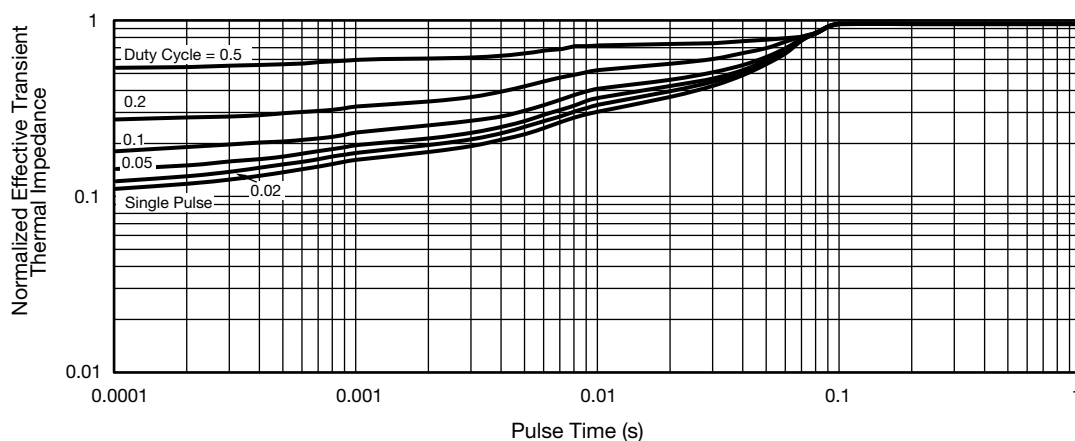
**THERMAL RESISTANCE RATINGS**

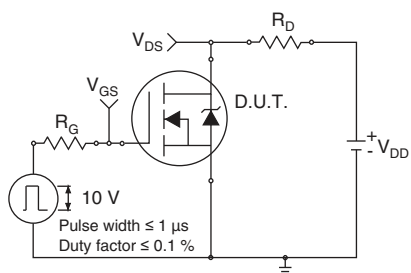
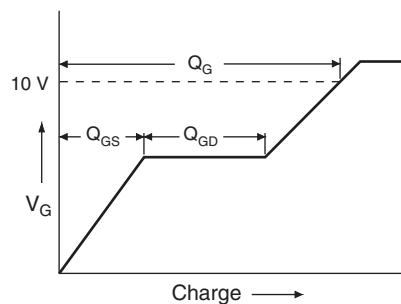
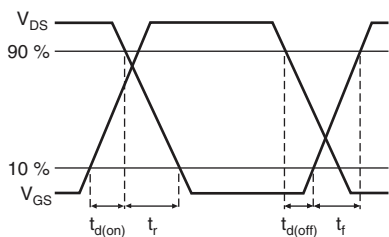
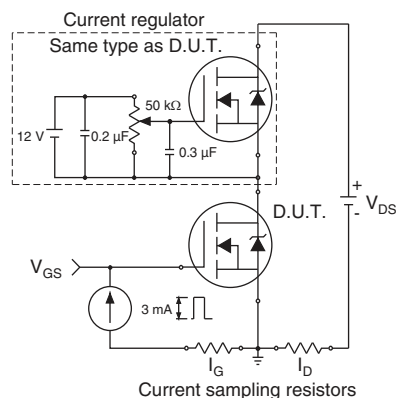
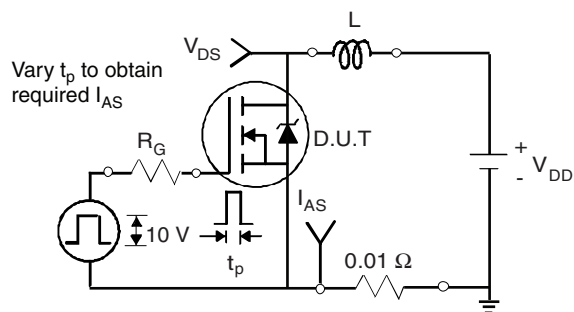
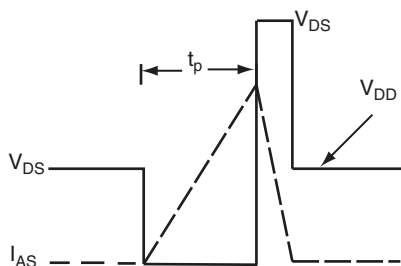
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

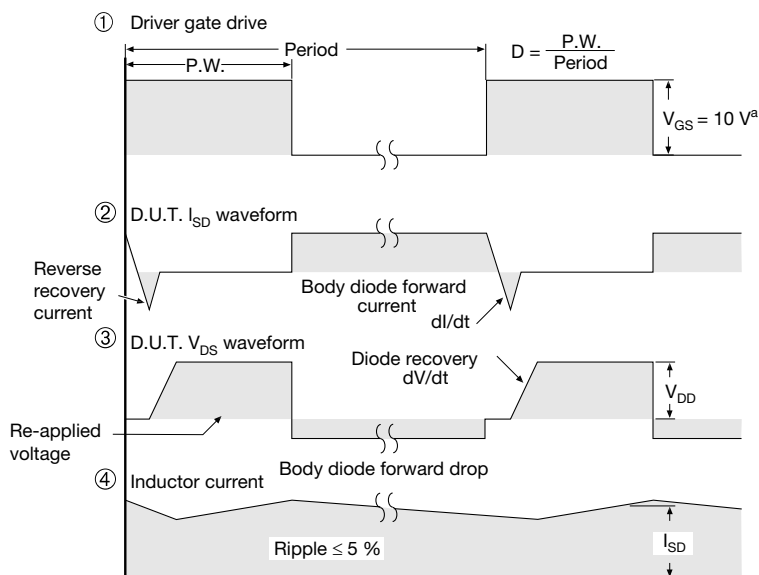
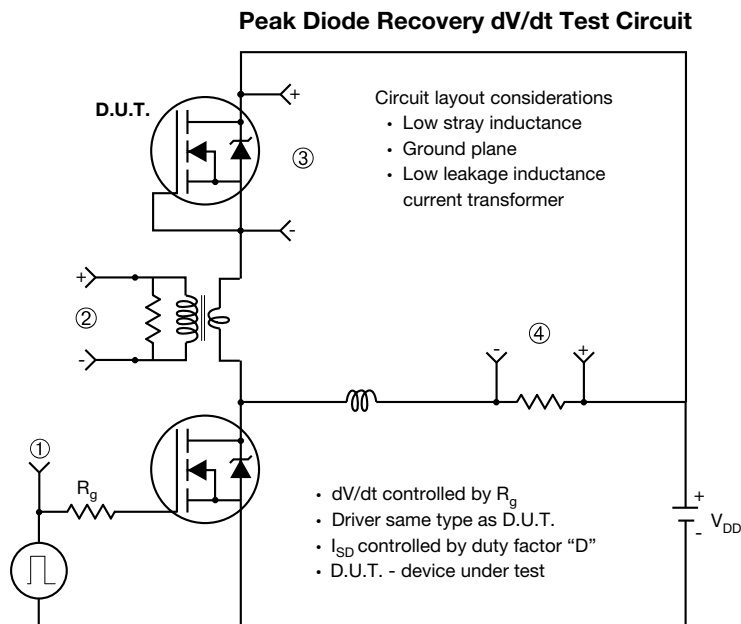
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		400	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 250 μA		-	0.5	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		3	-	5	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 30 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 320 V, V _{GS} = 0 V, T _J = 125 °C		-	-	10	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 13 A	-	0.14	0.17	Ω
Forward Transconductance	g _{fs}	V _{DS} = 50 V, I _D = 13 A		-	7.4	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	1707	-	pF
Output Capacitance	C _{oss}			-	177	-	
Reverse Transfer Capacitance	C _{rss}			-	19	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 13 A, V _{DS} = 320 V	-	44	88	nC
Gate-Source Charge	Q _{gs}			-	12	-	
Gate-Drain Charge	Q _{gd}			-	23	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 320 V, I _D = 13 A, V _{GS} = 10 V, R _g = 24.6 Ω		-	21	42	ns
Rise Time	t _r			-	57	86	
Turn-Off Delay Time	t _{d(off)}			-	40	80	
Fall Time	t _f			-	37	74	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	1.8	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	24	A
Pulsed Diode Forward Current	I _{SM}			-	-	78	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 13 A, V _{GS} = 0 V		-	-	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 13 A, dI/dt = 100 A/μs, V _R = 20 V		-	353	-	ns
Reverse Recovery Charge	Q _{rr}			-	4.4	-	μC
Reverse Recovery Current	I _{RRM}			-	24	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10 - Temperature vs. Drain-to-Source Voltage

Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case


Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

Fig. 13 - Switching Time Waveforms

Fig. 17 - Gate Charge Test Circuit

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms


Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

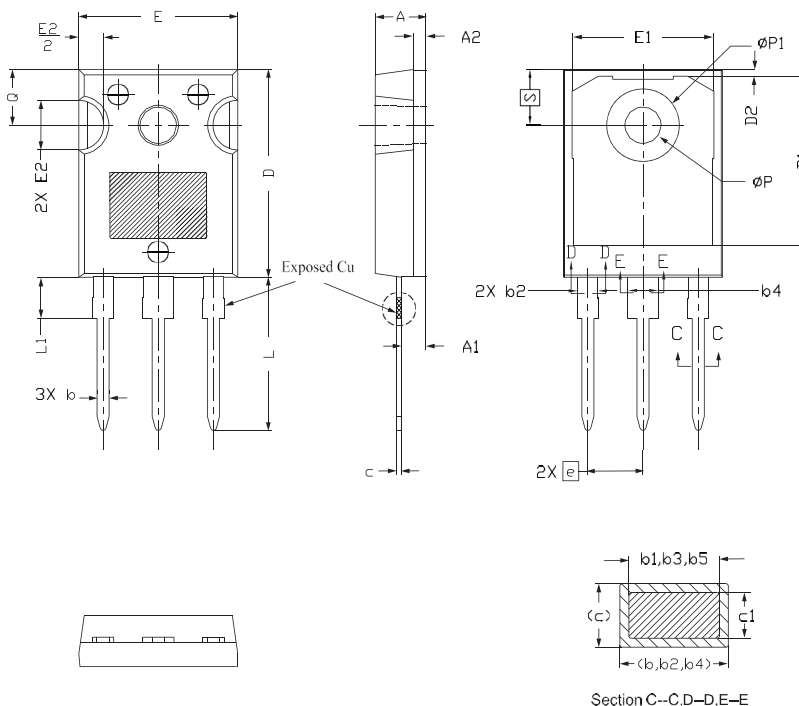
Fig. 18 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9



Section C--C,D--D,E--E

MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

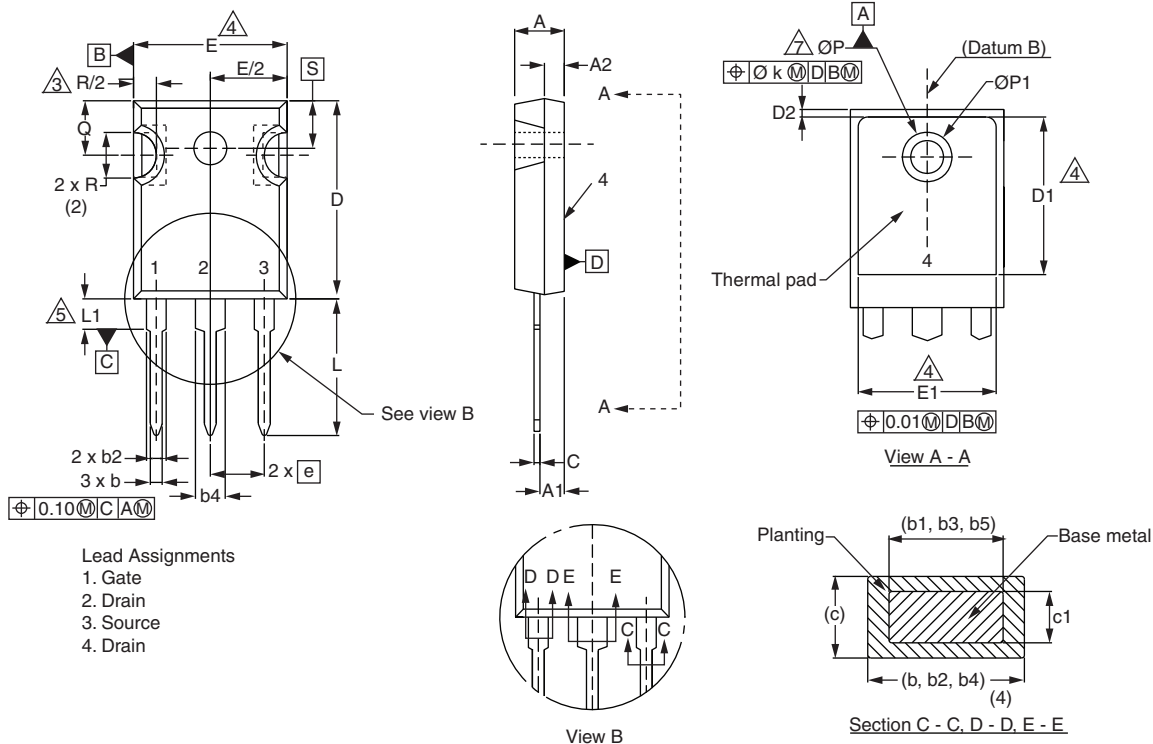
MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
e	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
Ø P	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S	5.51 BSC			

Notes

- Package reference: JEDEC® TO247, variation AC
- All dimensions are in mm
- Slot required, notch may be rounded
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions D1 and E1
- Lead finish uncontrolled in L1
- Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



VERSION 2: FACILITY CODE = Y



DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
c	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

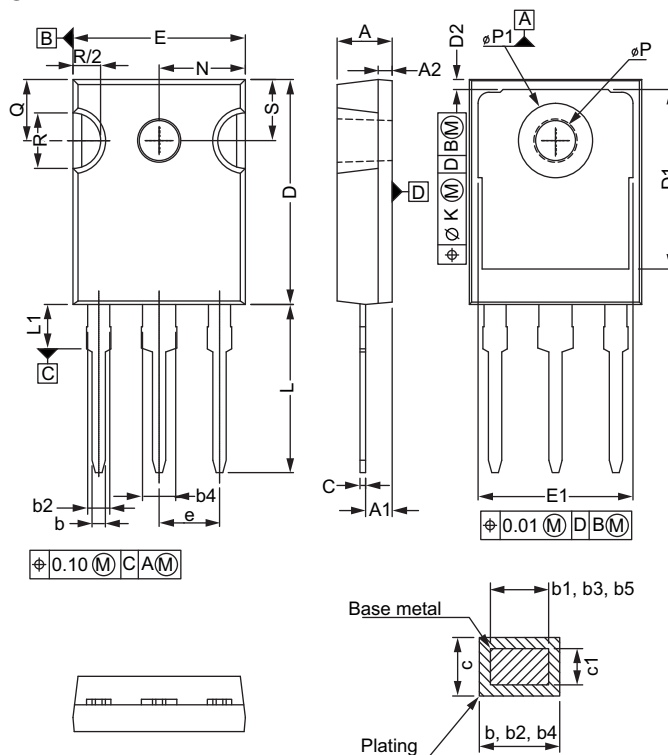
DIM.	MILLIMETERS		NOTES
	MIN.	MAX.	
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
e	5.46 BSC		
Ø k	0.254		
L	14.20	16.25	
L1	3.71	4.29	
Ø P	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Contour of slot optional
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions D1 and E1
- Lead finish uncontrolled in L1
- Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



MILLIMETERS		
DIM.	MIN.	MAX.
A	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
c	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

MILLIMETERS		
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
e	5.46 BSC	
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62 BSC	
P	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51 BSC	

ECN: E22-0452-Rev. G, 31-Oct-2022
DWG: 5971

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Contour of slot optional
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions D1 and E1
- Lead finish uncontrolled in L1
- Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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